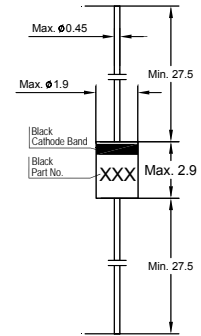


1SS244

Silicon Epitaxial Planar Diode

High voltage switching diode



Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	250	V
Reverse Voltage	V_R	220	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Peak Forward Current	I_{FM}	625	mA
Surge Forward Current (1 s)	I_{FSM}	1	A
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 65 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	V_F	1.5	V
Reverse Current at $V_R = 220\text{ V}$	I_R	10	μA
Capacitance between Terminals at $V_R = 0$, $f = 1\text{ MHz}$	C_T	3	pF
Reverse Recovery Time at $I_R = 20\text{ mA}$, $I_F = 20\text{ mA}$, $R_L = 50\text{ }\Omega$	t_{rr}	75	ns

